

## 162CMQ030 SCHOTTKY RECTIFIER

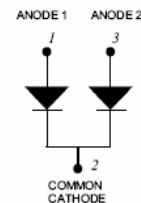
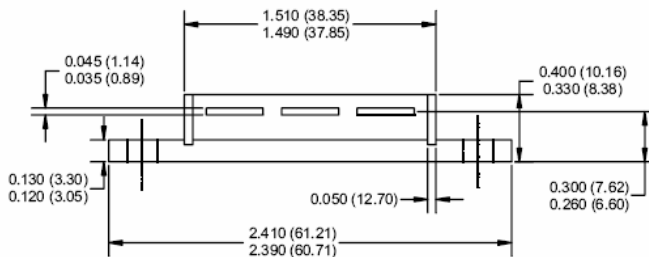
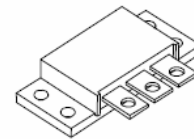
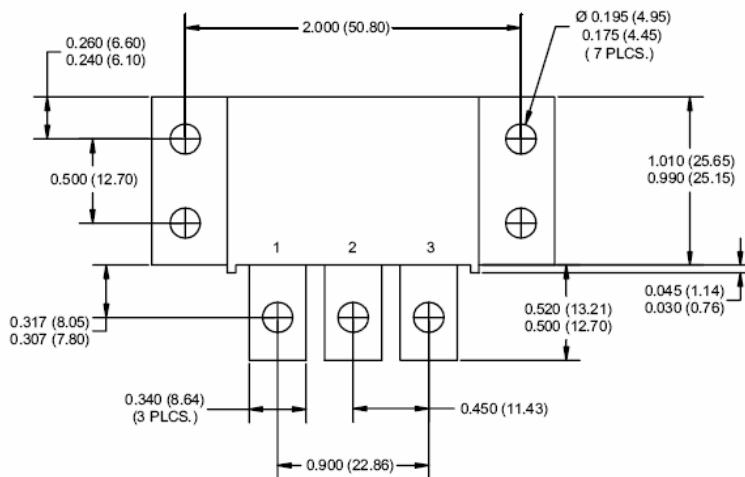
### Applications:

- Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

### Features:

- 150 °C T<sub>J</sub> operation
- Isolated heatsink
- Low profile, high current package
- Center tap module
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Mechanical Dimensions: In mm/Inches



### TO-249AA

#### MARKING, MOLDING RESIN

Marking for 162CMQ030, 1<sup>st</sup> row SS YYWWL, 2<sup>nd</sup> row 162CMQ030, 3<sup>rd</sup> row 1 2 3 (Pin)  
Where YY is the manufacture year  
WW is the manufacture week code  
L is the wafer's Lot Number

Molding resin

Epoxy resin UL: 94V-0

**Technical Data**  
**Data Sheet N1093, Rev. A**
**Green Products**
**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	30	V
Max. Average Forward*	$I_{F(AV)}$	50% duty cycle @ $T_C = 83^\circ\text{C}$ , rectangular wave form	160	A
Max. Peak One Cycle Non-Repetitive Surge Current (peg leg)	$I_{FSM}$	8.3 ms, half Sine pulse	1176	A
Non-Repetitive Avalanche Energy(peg leg)	$E_{AS}$	$T_J = 25^\circ\text{C}, I_{AS} = 16\text{A}, L = 0.56\text{mH}$	72	mJ
Repetitive Avalanche Current(peg leg)	$I_{AR}$	Current decaying linearly to zero in 1 $\mu\text{sec}$ Frequency limited by $T_J$ max. $V_A = 1.5 \times V_R$ typical	16	A

**Electrical Characteristics:**

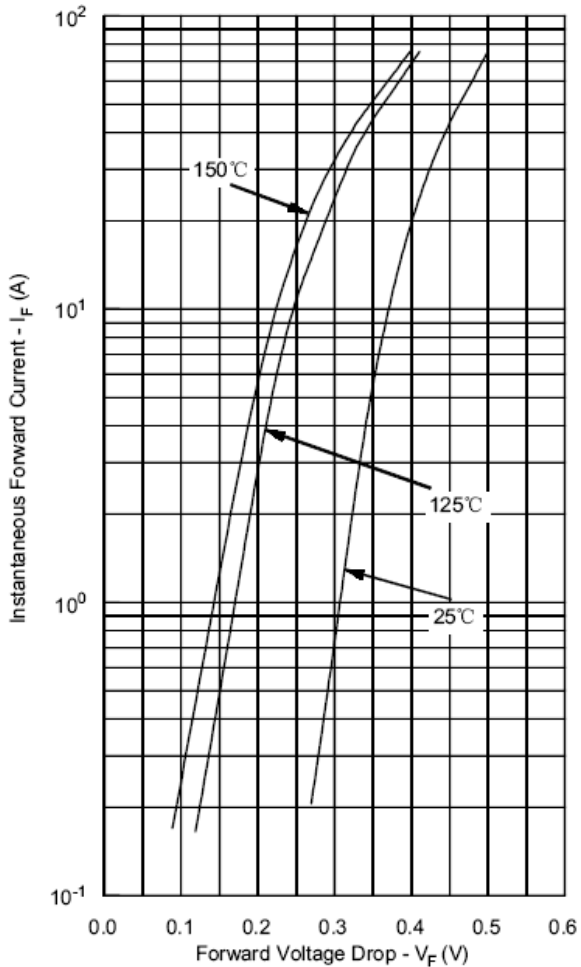
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	$V_{F1}$	@ 80A, Pulse, $T_J = 25^\circ\text{C}$ @ 160A, Pulse, $T_J = 25^\circ\text{C}$	0.53 0.65	V
	$V_{F2}$	@ 80A, Pulse, $T_J = 75^\circ\text{C}$ @ 160A, Pulse, $T_J = 75^\circ\text{C}$	0.46 0.63	V
Max. Reverse Current (per leg) *	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	5	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	280	mA
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 5\text{V}, T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	3700	pF
Typical Series Inductance (per leg)	$L_S$	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2%

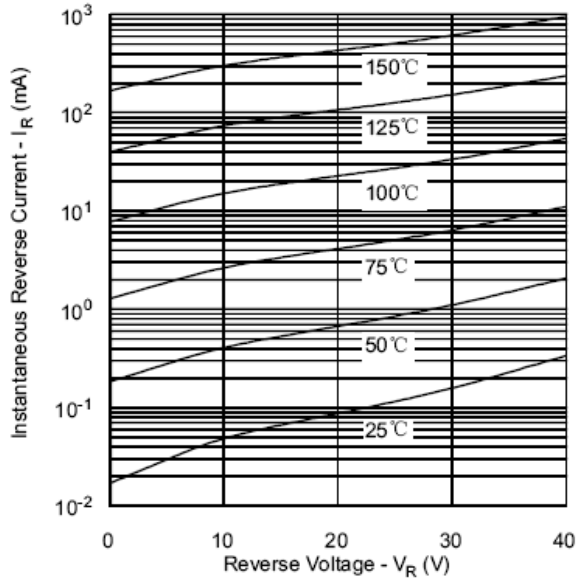
**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	0.70	$^\circ\text{C/W}$
Maximum Thermal Resistance Junction to Case (per package)	$R_{\theta JC}$	DC operation	0.35	$^\circ\text{C/W}$
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10	$^\circ\text{C/W}$
Mounting Torque	$T_M$	-	40(min)	Kg-cm
			58(max)	
Approximate Weight	wt	-	58	g
Case Style	TO-249AA			

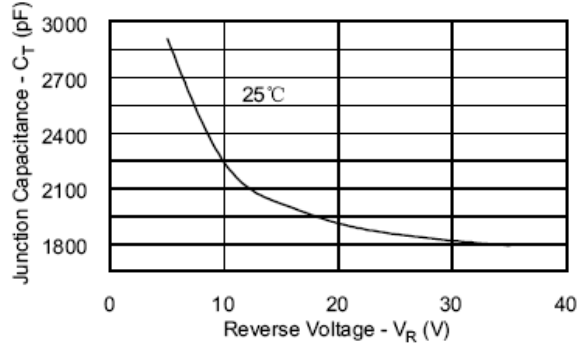
**Typical Forward Characteristics**



**Typical Reverse Characteristics**



**Typical Junction Capacitance**



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